



**THE DATASHEET OF
ST103S08PFN0**



INVERTER GRADE THYRISTORS

Stud Version

Features

- All diffused design
- Center amplifying gate
- Guaranteed high dv/dt
- Guaranteed high di/dt
- High surge current capability
- Low thermal impedance
- High speed performance

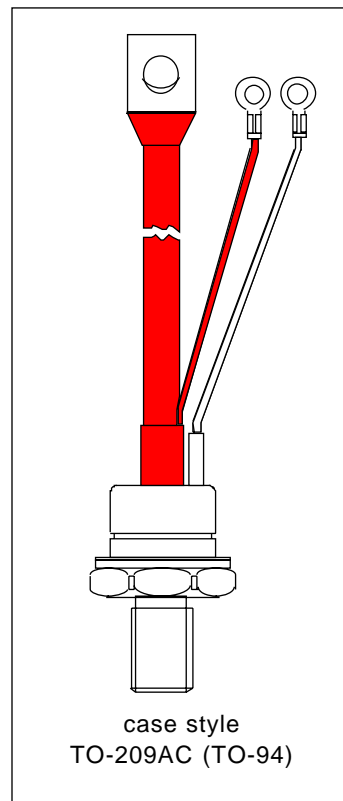
105A

Typical Applications

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

Major Ratings and Characteristics

| Parameters | ST103S | Units |
|-------------------|-------------|----------------------|
| $I_{T(AV)}$ | 105 | A |
| | @ T_C | 85 °C |
| $I_{T(RMS)}$ | 165 | A |
| I_{TSM} | @ 50Hz | 3000 A |
| | @ 60Hz | 3150 A |
| I^2t | @ 50Hz | 45 KA ² s |
| | @ 60Hz | 41 KA ² s |
| V_{DRM}/V_{RRM} | 400 to 800 | V |
| t_q range | 10 to 25 | μs |
| T_J | - 40 to 125 | °C |



ST103S Series

Bulletin I25183 rev. B 03/94

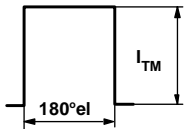
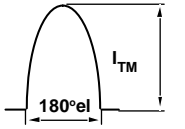
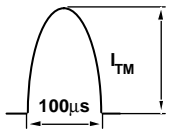
International
 TOR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

| Type number | Voltage Code | V_{DRM}/V_{RRM} , maximum repetitive peak voltage V | V_{RSM} , maximum non-repetitive peak voltage V | I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA |
|-------------|--------------|--|--|--|
| ST103S | 04 | 400 | 500 | 30 |
| | 08 | 800 | 900 | |

Current Carrying Capability

| Frequency |  | |  | |  | | Units |
|----------------------------------|---|-----|--|-----|---|------|-------|
| | | | | | | | |
| 50Hz | 280 | 180 | 440 | 330 | 4730 | 3630 | A |
| 400Hz | 310 | 200 | 470 | 300 | 2500 | 1850 | |
| 1000Hz | 320 | 200 | 480 | 310 | 1530 | 1090 | |
| 2500Hz | 340 | 210 | 490 | 320 | 840 | 580 | |
| Recovery voltage Vr | 50 | 50 | 50 | 50 | 50 | 50 | V |
| Voltage before turn-on Vd | V_{DRM} | | V_{DRM} | | V_{DRM} | | |
| Rise of on-state current di/dt | 50 | 50 | - | - | - | - | A/µs |
| Case temperature | 60 | 85 | 60 | 85 | 60 | 85 | °C |
| Equivalent values for RC circuit | 22Ω / 0.15µF | | 22Ω / 0.15µF | | 22Ω / 0.15µF | | |

On-state Conduction

| Parameter | ST103S | Units | Conditions | | |
|---|--------|--------------------|--|-----------------------|-----------------------|
| $I_{T(AV)}$ Max. average on-state current @ Case temperature | 105 | A | 180° conduction, half sine wave | | |
| | 85 | °C | | | |
| $I_{T(RMS)}$ Max. RMS on-state current | 165 | A | DC @ 76°C case temperature | | |
| I_{TSM} Max. peak, one half cycle, non-repetitive surge current | 3000 | | t = 10ms | No voltage reappplied | |
| | 3150 | | t = 8.3ms | reappplied | |
| | 2530 | | t = 10ms | 100% V_{RRM} | |
| | 2650 | | t = 8.3ms | reappplied | |
| I^2t Maximum I^2t for fusing | 45 | | KA ² s | t = 10ms | No voltage reappplied |
| | 41 | | | t = 8.3ms | reappplied |
| | 32 | | | t = 10ms | 100% V_{RRM} |
| | 29 | t = 8.3ms | | reappplied | |
| $I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing | 450 | KA ² √s | t = 0.1 to 10ms, no voltage reappplied | | |

On-state Conduction

| Parameter | ST103S | Units | Conditions |
|---|--------|------------|---|
| V_{TM} Max. peak on-state voltage | 1.73 | V | $I_{TM} = 300A$, $T_J = T_J \text{ max}$, $t_p = 10\text{ms}$ sine wave pulse |
| $V_{T(TO)1}$ Low level value of threshold voltage | 1.32 | | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$. |
| $V_{T(TO)2}$ High level value of threshold voltage | 1.35 | | $(I > \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$. |
| r_{t1} Low level value of forward slope resistance | 1.40 | m Ω | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$. |
| r_{t2} High level value of forward slope resistance | 1.30 | | $(I > \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$. |
| I_H Maximum holding current | 600 | mA | $T_J = 25^\circ\text{C}$, $I_T > 30A$ |
| I_L Typical latching current | 1000 | | $T_J = 25^\circ\text{C}$, $V_A = 12V$, $R_a = 6\Omega$, $I_G = 1A$ |

Switching

| Parameter | ST103S | Units | Conditions |
|---|--------------------|------------------|--|
| di/dt Max. non-repetitive rate of rise of turned-on current | 1000 | A/ μs | $T_J = T_J \text{ max}$, $V_{DRM} = \text{rated } V_{DRM}$ $I_{TM} = 2 \times \text{di/dt}$ |
| t_d Typical delay time | 0.80 | μs | $T_J = 25^\circ\text{C}$, $V_{DM} = \text{rated } V_{DRM}$, $I_{TM} = 50A \text{ DC}$, $t_p = 1\mu\text{s}$ Resistive load, Gate pulse: 10V, 5 Ω source |
| t_q Max. turn-off time | Min: 10 Max: 25 | | $T_J = T_J \text{ max}$, $I_{TM} = 100A$, commutating di/dt = 10A/ μs $V_R = 50V$, $t_p = 200\mu\text{s}$, dv/dt: see table in device code |

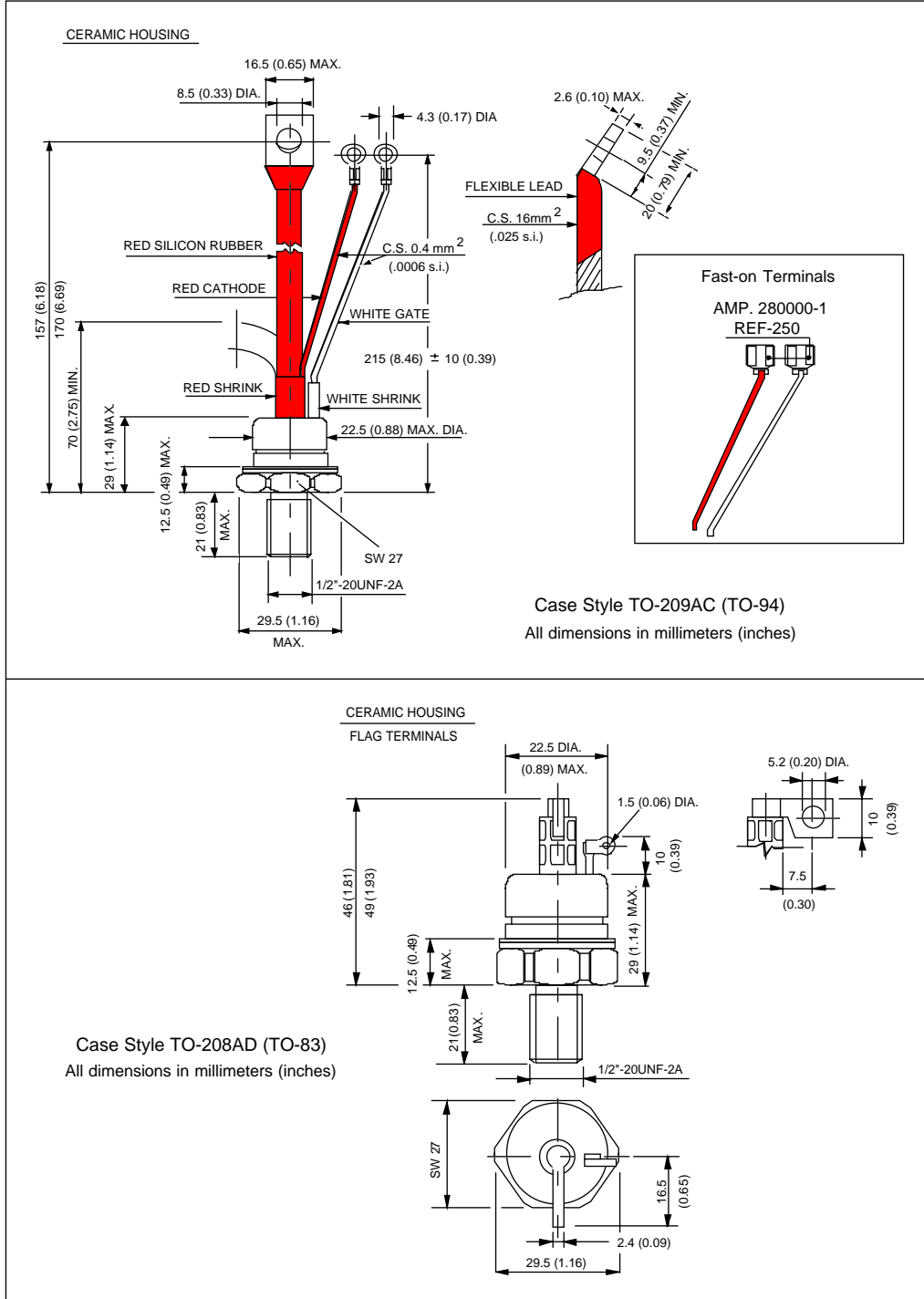
Blocking

| Parameter | ST103S | Units | Conditions |
|---|--------|------------------|--|
| dv/dt Maximum critical rate of rise of off-state voltage | 500 | V/ μs | $T_J = T_J \text{ max}$., linear to 80% V_{DRM} , higher value available on request |
| I_{DRM}^{RRM} Max. peak reverse and off-state leakage current | 30 | mA | $T_J = T_J \text{ max}$, rated V_{DRM}/V_{RRM} applied |

Triggering

| Parameter | ST103S | Units | Conditions |
|---|--------|-------|--|
| P_{GM} Maximum peak gate power | 40 | W | $T_J = T_J \text{ max}$, $f = 50\text{Hz}$, $d\% = 50$ |
| $P_{G(AV)}$ Maximum average gate power | 5 | | |
| I_{GM} Max. peak positive gate current | 5 | A | $T_J = T_J \text{ max}$, $t_p \leq 5\text{ms}$ |
| $+V_{GM}$ Maximum peak positive gate voltage | 20 | V | $T_J = T_J \text{ max}$, $t_p \leq 5\text{ms}$ |
| $-V_{GM}$ Maximum peak negative gate voltage | 5 | | |
| I_{GT} Max. DC gate current required to trigger | 200 | mA | $T_J = 25^\circ\text{C}$, $V_A = 12V$, $R_a = 6\Omega$ |
| V_{GT} Max. DC gate voltage required to trigger | 3 | | |
| I_{GD} Max DC gate current not to trigger | 20 | mA | $T_J = T_J \text{ max}$, rated V_{DRM} applied |
| V_{GD} Max. DC gate voltage not to trigger | 0.25 | | |

Outline Table



ST103S Series

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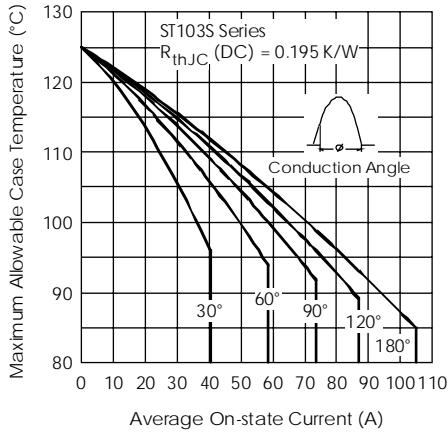


Fig. 1 - Current Ratings Characteristics

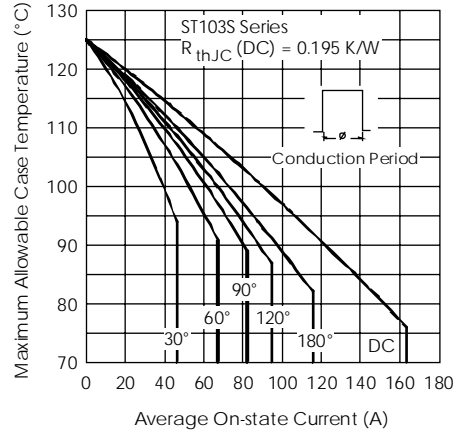


Fig. 2 - Current Ratings Characteristics

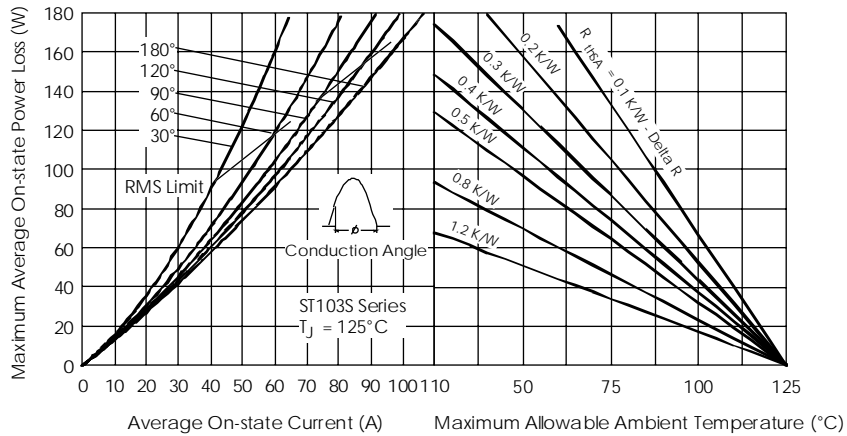


Fig. 3 - On-state Power Loss Characteristics

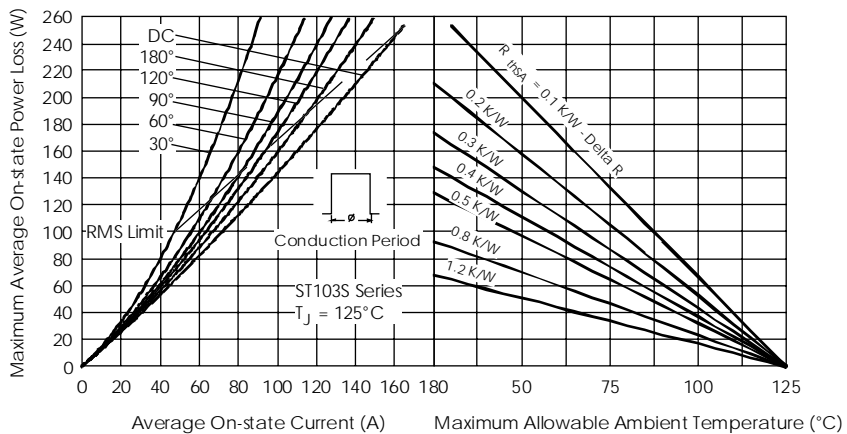


Fig. 4 - On-state Power Loss Characteristics

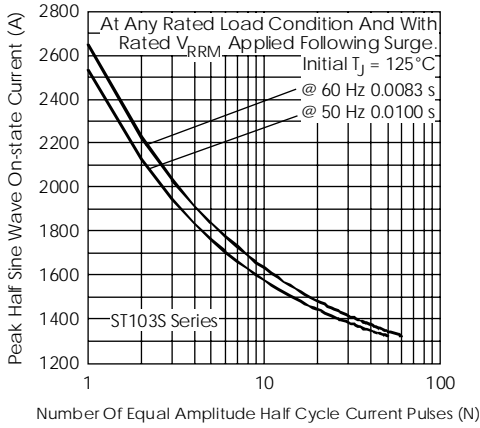


Fig. 5 - Maximum Non-repetitive Surge Current

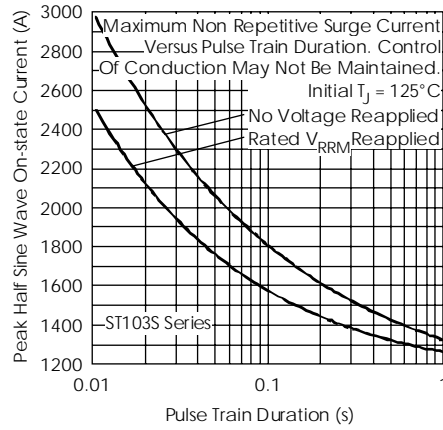


Fig. 6 - Maximum Non-repetitive Surge Current

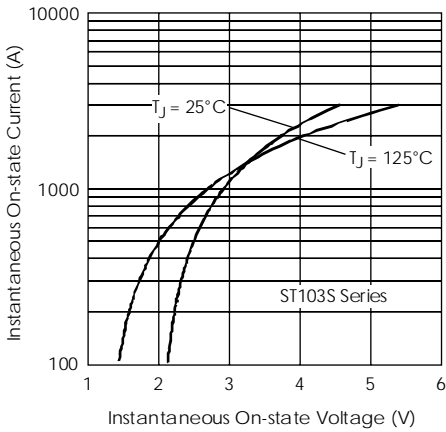


Fig. 7 - On-state Voltage Drop Characteristics

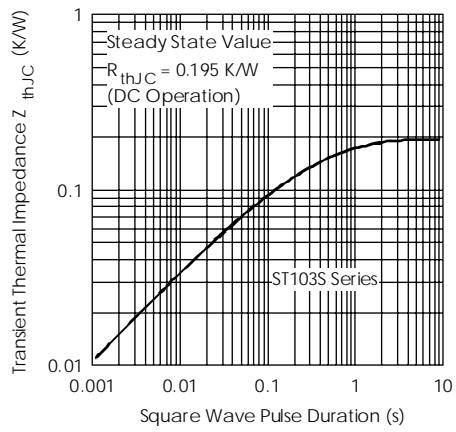


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

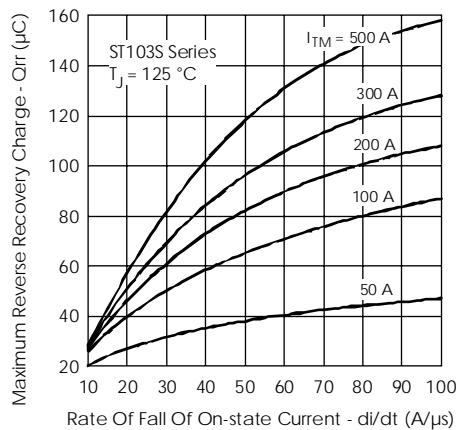


Fig. 9 - Reverse Recovered Charge Characteristics

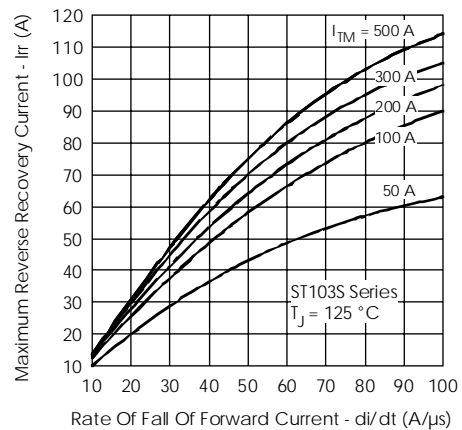


Fig. 10 - Reverse Recovery Current Characteristics

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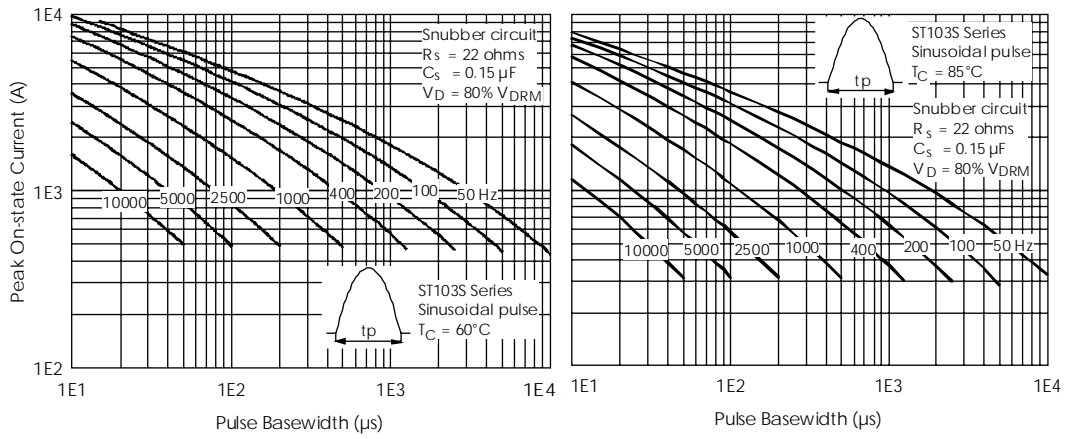


Fig. 11 - Frequency Characteristics

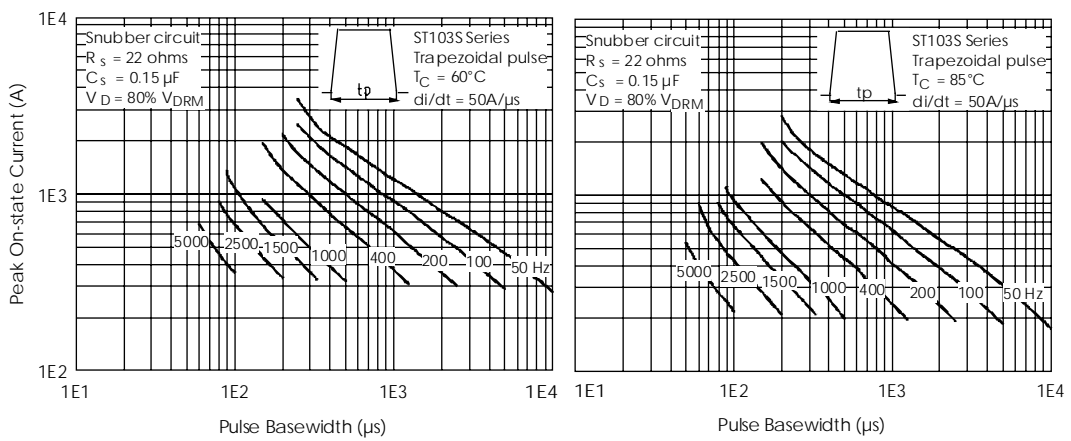


Fig. 12 - Frequency Characteristics

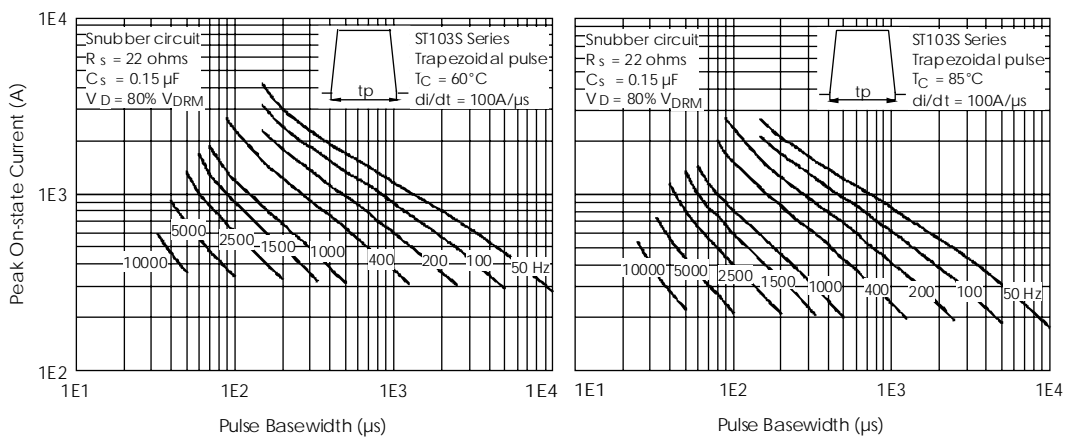


Fig. 13 - Frequency Characteristics

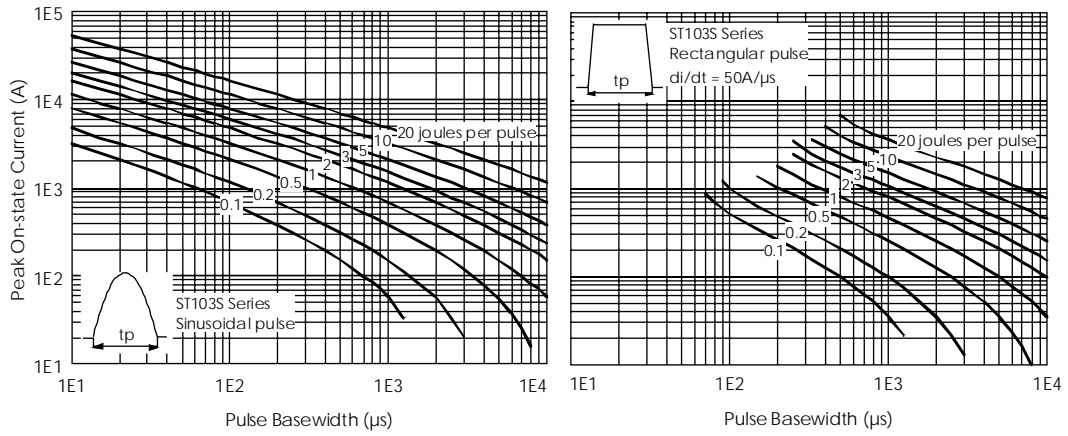


Fig. 14 - Maximum On-state Energy Power Loss Characteristics

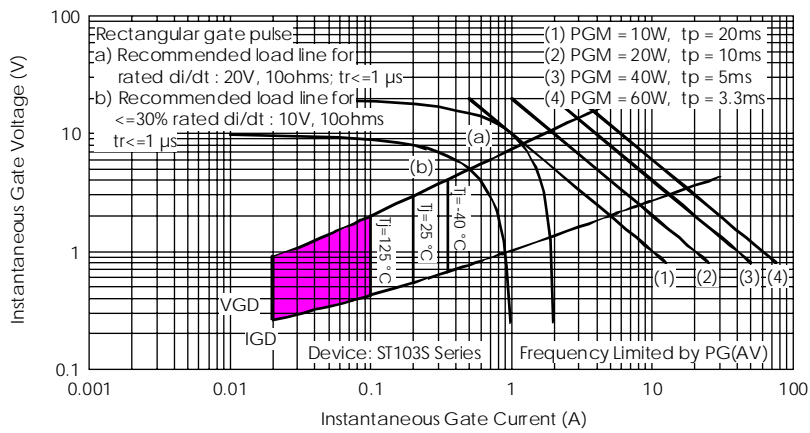


Fig. 15 - Gate Characteristics



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